COMPLIANT

HALOGEN FREE





P-Channel 20 V (D-S) MOSFET

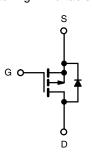
PRODUCT SUMMARY					
V _{DS} (V)	$R_{DS(on)}(\Omega)$	I _D (A)			
- 20	0.0108 at V _{GS} = - 4.5 V	- 15.3			
	0.015 at V _{GS} = - 2.5 V	- 13.0			
	0.020 at V _{GS} = - 1.8 V	- 11.2			

FEATURES

- Halogen-free According to IEC 61249-2-21 Definition
- TrenchFET[®] Power MOSFET: 1.8 V Rated
- Ultra Low On-Resistance for Increased Battery Life
- New PowerPAK[®] Package
 - Low Thermal Resistance, R_{thJC}
 - Low 1.07 mm Profile
- · Compliant to RoHS Directive 2002/95/EC



• Load/Power Switching in Portable Devices



P-Channel MOSFET

FOWEIFAR 1212-0
3.30 mm 3.30 mm 3.30 mm 2.5 3.30 mm

Bottom View

PowerPAK 1212-8

Ordering Information: Si7107DN-T1-E3 (Lead (Pb)-free)

Si7107DN-T1-GE3 (Lead (Pb)-free and Halogen-free)

ABSOLUTE MAXIMUM RATINGS	T _A = 25 °C, unle	ss otherwise n	oted		
Parameter		Symbol	10 s	Steady State	Unit
Drain-Source Voltage		V _{DS}	- 20		V
Gate-Source Voltage		V _{GS}	± 8		
Continuous Drain Current (T _J = 150 °C) ^a	T _A = 25 °C	- I _D	- 15.3	- 9.8	^
	T _A = 70 °C		- 12.2	- 7.8	
Pulsed Drain Current		I _{DM}	- 40		Α
Continuous Source Current (Diode Conduction) ^a		I _S	- 3.2	- 1.3	
Maximum Power Dissipation ^a	T _A = 25 °C	P _D	3.8	1.5	W
	T _A = 70 °C		2.4	1.0	
Operating Junction and Storage Temperature Range		T _J , T _{stg}	- 55 to 150		°C
Soldering Recommendations (Peak Temperature) ^{b, c}			260		

THERMAL RESISTANCE RATINGS						
Parameter		Symbol	Typical	Maximum	Unit	
Mariano de Location de Ambienda	t ≤ 10 s	- R _{thJA}	24	33	°C/W	
Maximum Junction-to-Ambient ^a	Steady State		65	81		
Maximum Junction-to-Case	Steady State	R_{thJC}	1.9	2.4		

Notes:

- a. Surface Mounted on 1" x 1" FR4 board.
- b. See Solder Profile (www.vishay.com/ppg?73257). The PowerPAK 1212-8 is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.
- c. Rework Conditions: manual soldering with a soldering iron is not recommended for leadless components.

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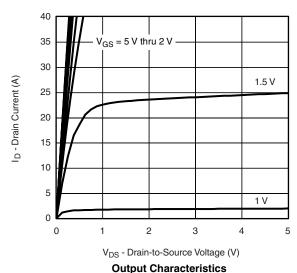
SPECIFICATIONS T _J = 25 °C, unless otherwise noted								
Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit		
Static								
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_{D} = -450 \mu A$	- 0.4		- 1.0	V		
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 8 \text{ V}$			± 100	nA		
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = - 20 V, V _{GS} = 0 V			- 1			
		V _{DS} = - 20 V, V _{GS} = 0 V, T _J = 55 °C			- 5	μΑ		
On-State Drain Current ^a	I _{D(on)}	$V_{DS} \le -5 \text{ V}, V_{GS} = -4.5 \text{ V}$	- 40			Α		
		V _{GS} = - 4.5 V, I _D = - 15.3 A		0.0090	0.0108	Ω		
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = - 2.5 V, I _D = - 13 A		0.0125	0.015			
		V _{GS} = - 1.8 V, I _D = - 5 A		0.0167	0.020			
Forward Transconductance ^a	9 _{fs}	V _{DS} = - 15 V, I _D = - 15.3 A		58		S		
Diode Forward Voltage ^a	V_{SD}	I _S = - 3.2 A, V _{GS} = 0 V		- 0.7	- 1.2	V		
Dynamic ^b								
Total Gate Charge	Qg			34	44			
Gate-Source Charge	Q_{gs}	$V_{DS} = -10 \text{ V}, V_{GS} = -4.5 \text{ V}, I_{D} = -15.3 \text{ A}$		4.6		nC		
Gate-Drain Charge	Q_{gd}			9.2				
Gate Resistance	R_g	f = 1 MHz		8		Ω		
Turn-On Delay Time	t _{d(on)}			27	40			
Rise Time	t _r	V_{DD} = - 10 V, R_L = 10 Ω		55	85			
Turn-Off Delay Time	t _{d(off)}	$I_D \cong$ - 1 A, V_{GEN} = - 4.5 V, R_g = 6 Ω		270	400	ns		
Fall Time	t _f			160	240			
Source-Drain Reverse Recovery Time	t _{rr}	I _F = - 3.2 A, dl/dt = 100 A/μs		110	165			

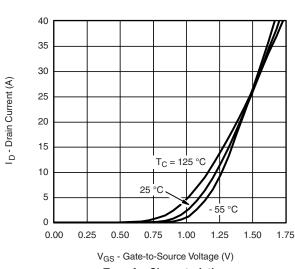
Notes:

- a. Pulse test; pulse width $\leq 300~\mu s,$ duty cycle $\leq 2~\%.$
- b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



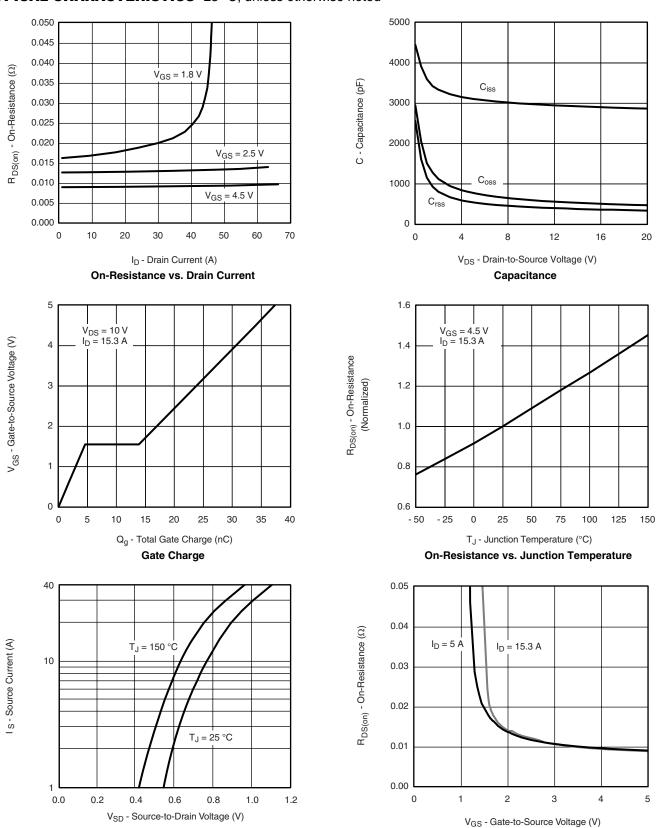


Transfer Characteristics





TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



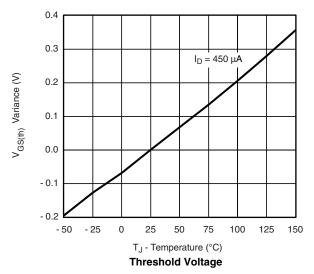
Source-Drain Diode Forward Voltage

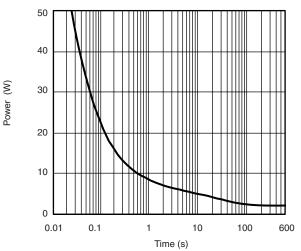
On-Resistance vs. Gate-to-Source Voltage

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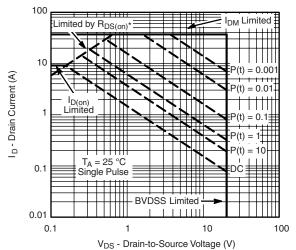
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TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



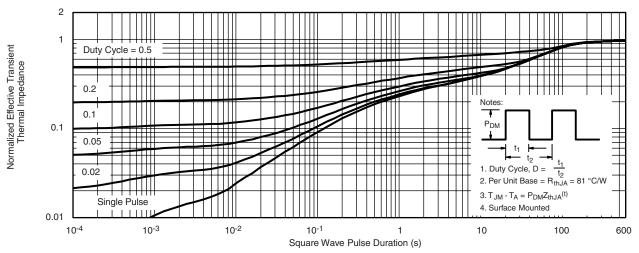


Single Pulse Power, Junction-to-Ambient



* V_{GS} > minimum V_{GS} at which R_{DS(on)} is specified

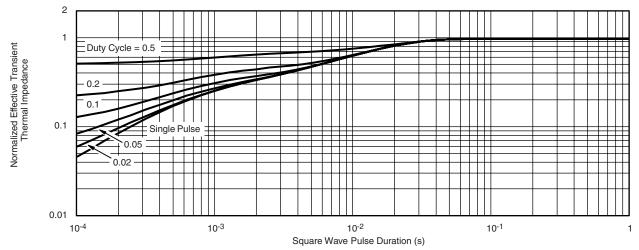
Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Ambient



TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



Normalized Thermal Transient Impedance, Junction-to-Case

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